MJ N-Channel Super Trench II Power MOSFET

Description

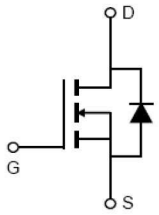
The series of devices uses Super Trench II technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Qg. This device is ideal for high-frequency switching and synchronous rectification.

General Features

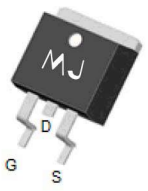
- V_{DS} =120V,I_D =90A
  $R_{DS(ON)}$ <7.5mΩ @ V_{GS}=10V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175°C operating temperature
- Pb-free lead plating

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic Diagram



TO-263

100% UIS TESTED! 100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
MJXP080N12D	MJXP080N12D	TO-263	-	-	-

Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	90	A
Drain Current-Continuous(T_C =100℃)	$I_{D(100℃)}$	64	A
Pulsed Drain Current (Note 1)	I_{DM}	360	A
Maximum Power Dissipation	P_D	140	W
Derating factor		0.93	W/℃
Single pulse avalanche energy (Note 4)	E_{AS}	352	mJ
Operating Junction and Storage Temperature Range	T_J ,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	1.07	℃/W

Electrical Characteristics (T_C=25℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	120	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=120V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{DS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} ,I_D=250μA	2.0	3.0	4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=45A	-	7.7	8.0	mΩ
		V_{GS}=10V, I_D=45A	-	7.5	8.0	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=45A	-	55	-	S
Dynamic Characteristics (Note 3)						
Input Capacitance	C_{lss}	V_{DS}=60V,V_{GS}=0V F=1.0MHz	-	3715	-	PF
Output Capacitance	C_{oss}		-	275	-	PF
Reverse Transfer Capacitance	C_{rss}		-	18	-	PF
Switching Characteristics (Note 3)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=60V,I_D=45A V_{GS}=10V,R_G=1.6Ω	-	20	-	nS
Turn-on Rise Time	t_r		-	16	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	45	-	nS
Turn-Off Fall Time	t_f		-	12	-	nS
Total Gate Charge	Q_g	V_{DS}=60V,I_D=45A V_{GS}=10V	-	58	-	nC
Gate-Source Charge	Q_{gs}		-	21	-	nC
Gate-Drain Charge	Q_{gd}		-	14.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 2)	V_{SD}	V_{GS}=0V,I_S=45A	-	-	1.2	V
Diode Forward Current	I_S		-	-	90	A
Reverse Recovery Time	t_{rr}	T_J=25°C, I_F=90A di/dt=100A/μs (Note 3)	-	65	-	nS
Reverse Recovery Charge	Q_{rr}		-	105	-	nC

Notes:

① Repetitive Rating: Pulse width limited by maximum junction temperature.
② Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
③ Guaranteed by design, not subject to production
④ EAS condition : T_J=25℃,V_{DD}=50V,V_G=10V,L=0.25mH,Rg=25Ω

Typical Electrical and Thermal Characteristics

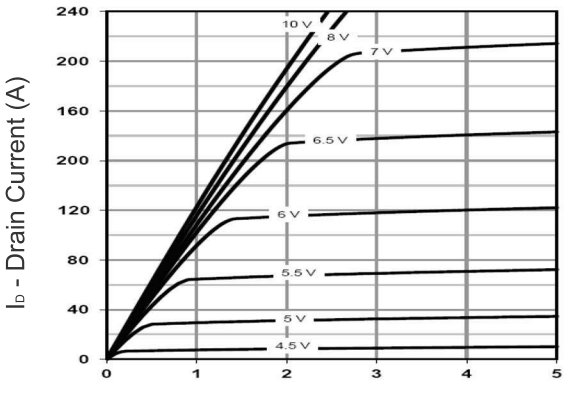


Figure 1 Output Characteristics

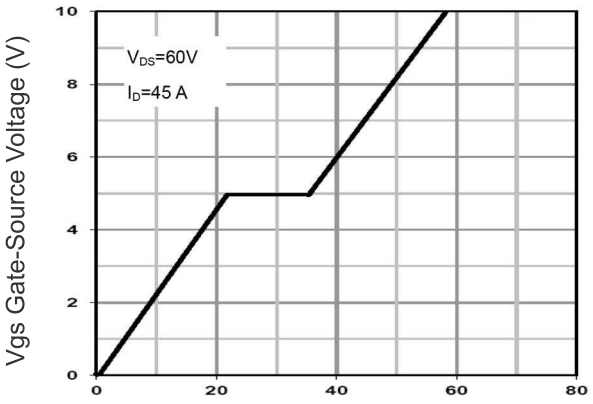


Figure 4 Gate Charge

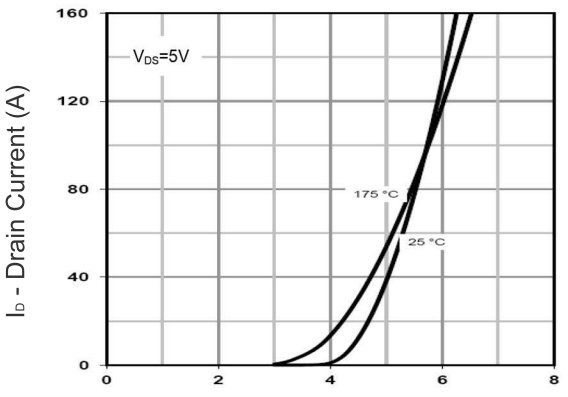


Figure 2 Transfer Characteristics

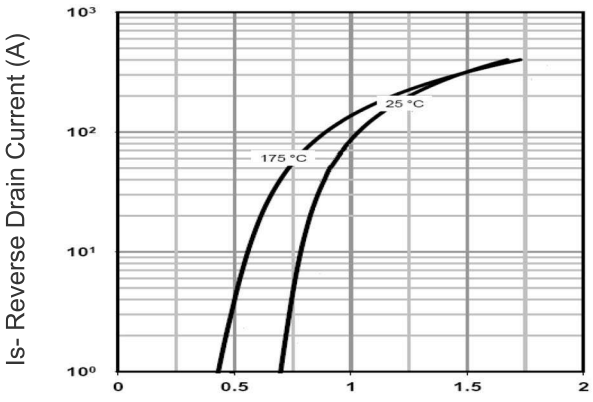


Figure 5 Source- Drain Diode Forward

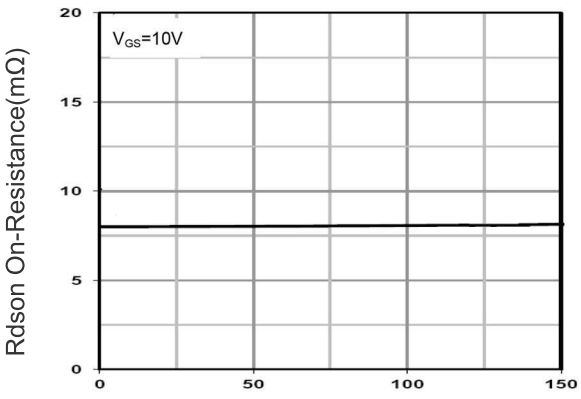


Figure 3 Rdson-Junction Temperature

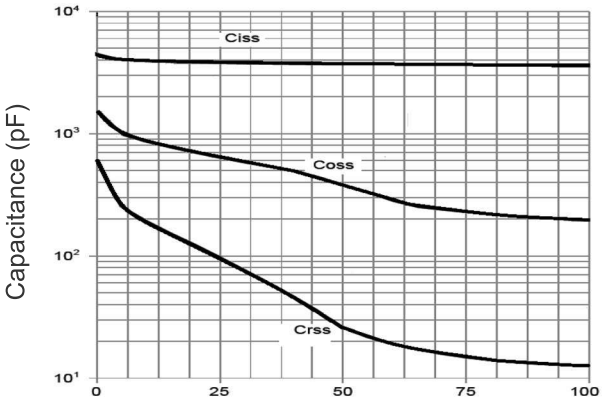
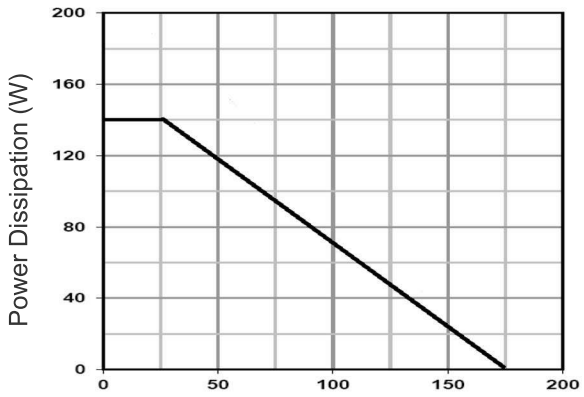
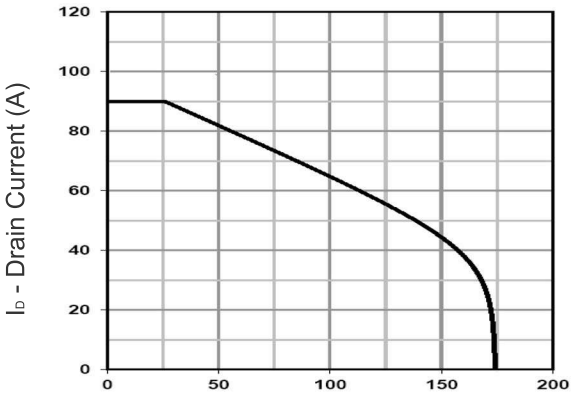


Figure 6 Capacitance vs Vds



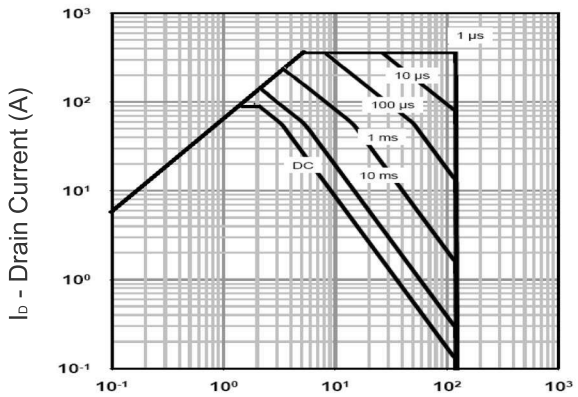
T_J -Junction Temperature(℃)

Figure 7 Power De-rating



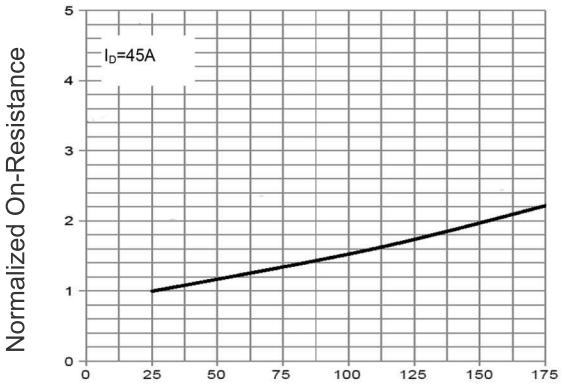
T_J -Junction Temperature(℃)

Figure 9 Current De-rating



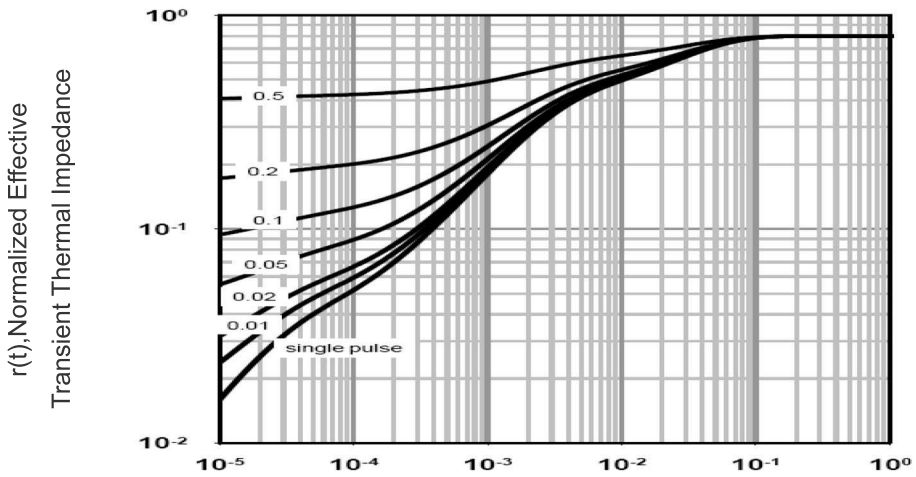
Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area



T_J -Junction Temperature(℃)

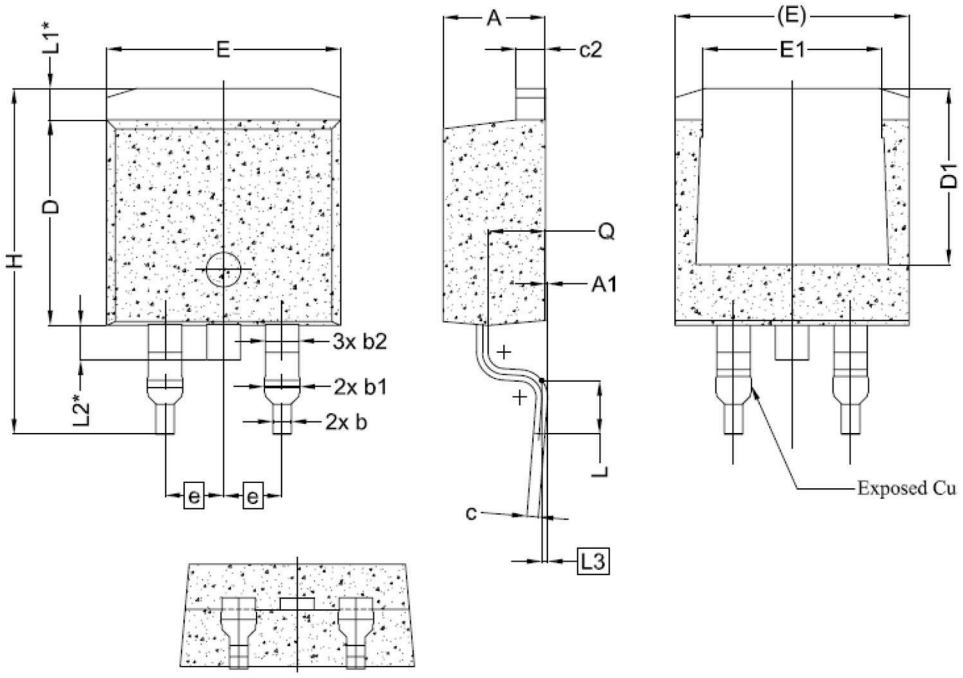
Figure 10 Rdson-Junction Temperature



Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	-
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

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